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2D Materials and Interfaces in High-Carrier Density Regime

A Study on Optoelectronics and Superconductivity

Abdurrahman Ali El Yumin

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A Study on Optoelectronics and Superconductivity

Phd Thesis

to obtain the degree of PhD at the
 University of Groningen
 on the authority of the
 Rector Magnificus Prof. C. Wijmenga
 and in accordance with
 the decision by the College of Deans.

This thesis will be defended in public on

Friday 30 August 2019 at 16.15 hours

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